

# Trench Schottky Rectifier, Very Low Leakage

## NRVTSS3100E

**SCHOTTKY BARRIER  
 RECTIFIERS  
 3 AMPERES  
 100 VOLTS**

### Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- High Surge Capability
- NRV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free and Halide-Free Devices

### Typical Applications

- Switching Power Supplies including Wireless, Smartphone and Notebook Adapters
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation
- LED Lighting

### Mechanical Characteristics:

- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in.
- Lead Finish: 100% Matte Sn (Tin)
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Device Meets MSL 1 Requirements



**SMB  
 CASE 403A**

### MARKING DIAGRAM



- TE31 = Specific Device Code
- A = Assembly Location
- Y = Year
- WW = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

# NRVTSS3100E

## MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	100	V
Average Rectified Forward Current ( $T_L = 142^\circ\text{C}$ )	$I_{F(AV)}$	3.0	A
Peak Repetitive Forward Current, (Square Wave, 20 kHz, $T_L = 135^\circ\text{C}$ )	$I_{FRM}$	6	A
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	$I_{FSM}$	90	A
Storage Temperature Range	$T_{stg}$	-65 to +175	$^\circ\text{C}$
Operating Junction Temperature	$T_J$	-55 to +175	$^\circ\text{C}$
ESD Rating (Human Body Model)		1B	
ESD Rating (Charged Device Model)		> 1000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Typ	Max	Unit
Thermal Resistance, Junction-to-Lead, Steady State (Assumes 600 mm <sup>2</sup> 1 oz. copper bond pad, on a FR4 board)	$R_{\theta JL}$	-	17.5	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient, Steady State (Assumes 600 mm <sup>2</sup> 1 oz. copper bond pad, on a FR4 board)	$R_{\theta JA}$	-	90	$^\circ\text{C}/\text{W}$

## ELECTRICAL CHARACTERISTICS

Instantaneous Forward Voltage (Note 1) ( $i_F = 3.0$ Amps, $T_J = 25^\circ\text{C}$ )  ( $i_F = 3.0$ Amps, $T_J = 125^\circ\text{C}$ )	$v_F$	0.88	0.995	V
		0.66	0.7	
Reverse Current (Note 1) (Rated dc Voltage, $T_J = 25^\circ\text{C}$ ) (Rated dc Voltage, $T_J = 125^\circ\text{C}$ )	$i_R$	0.9	5.0	$\mu\text{A}$
		0.62	2.0	mA
Diode Capacitance (Rated dc Voltage, $T_J = 25^\circ\text{C}$ , $f = 1$ MHz)	$C_d$	14.4		pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

TYPICAL CHARACTERISTICS

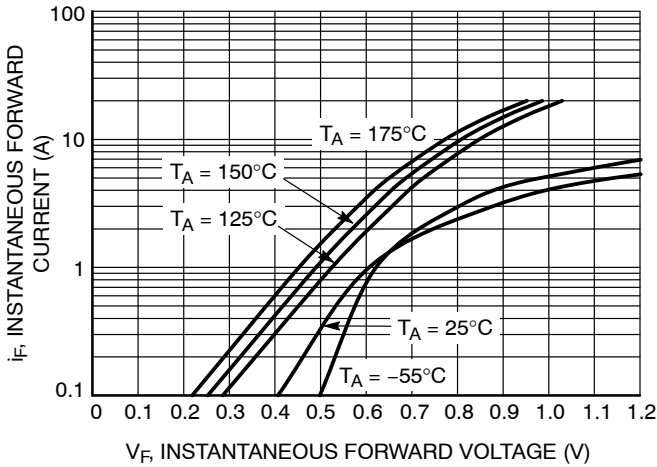


Figure 1. Typical Instantaneous Forward Characteristics

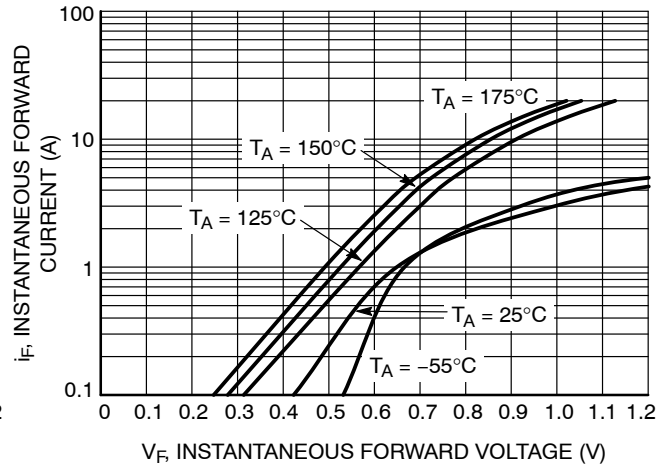


Figure 2. Maximum Instantaneous Forward Characteristics

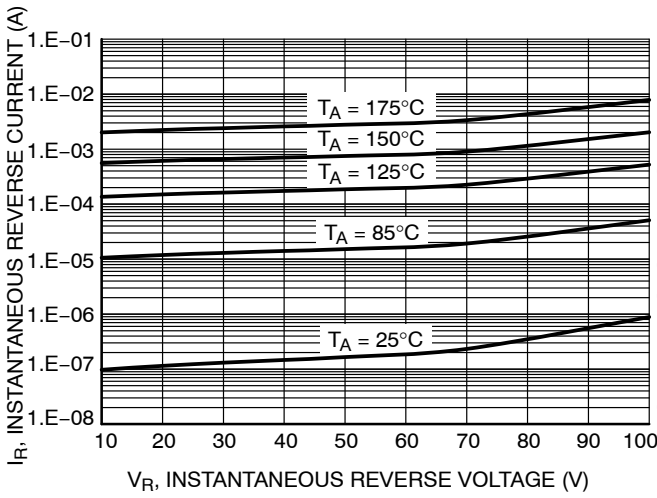


Figure 3. Typical Reverse Characteristics

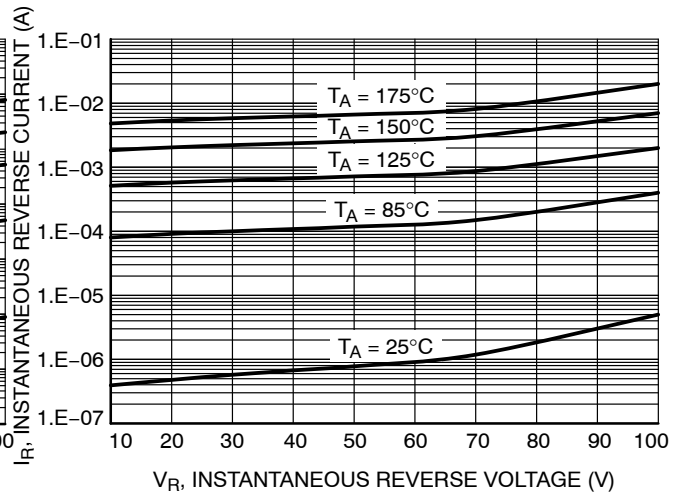


Figure 4. Maximum Reverse Characteristics

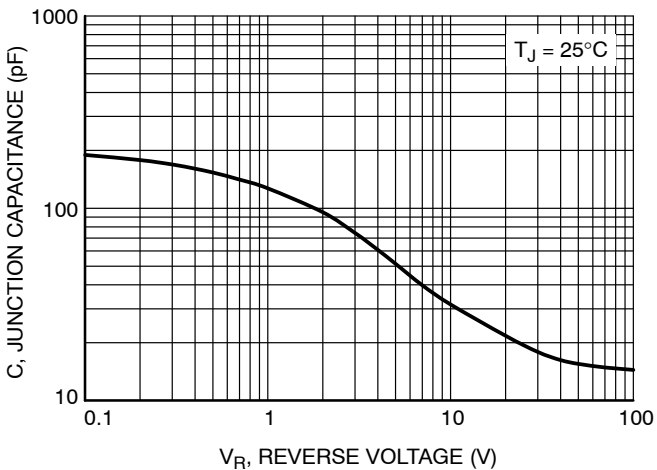


Figure 5. Typical Junction Capacitance

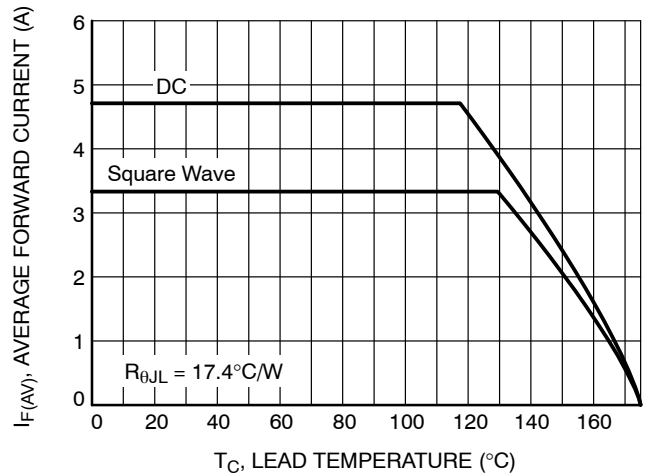


Figure 6. Current Derating

# NRVTSS3100E

## TYPICAL CHARACTERISTICS

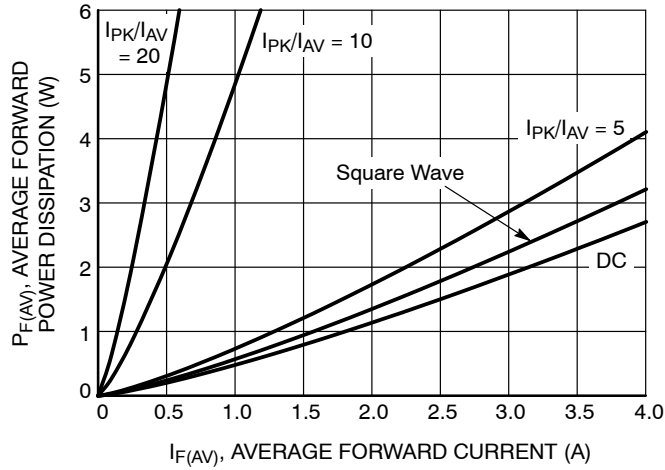


Figure 7. Forward Power Dissipation

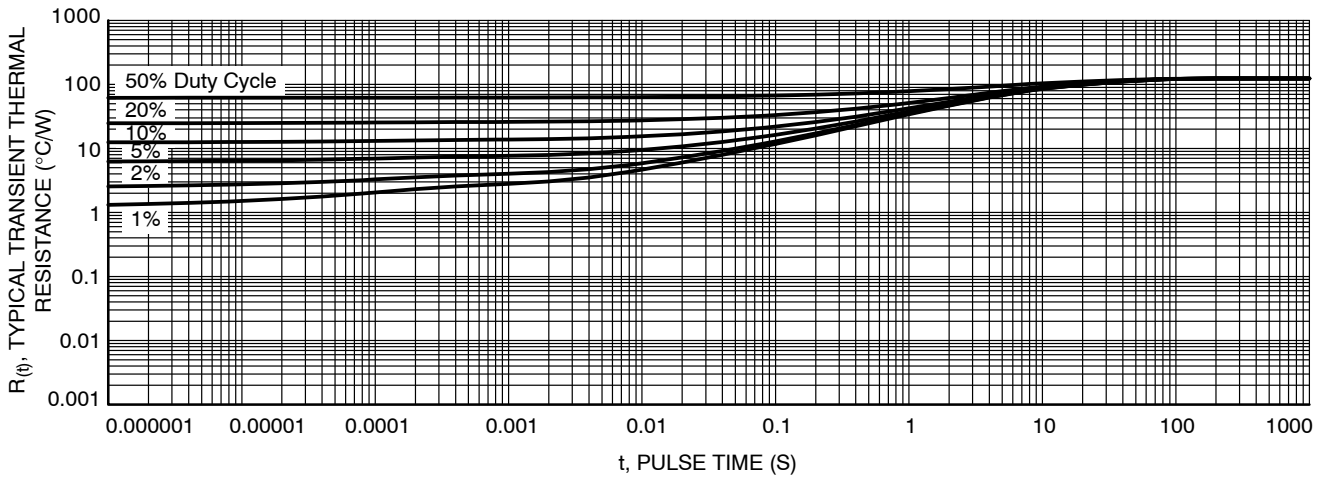


Figure 8. Typical Transient Thermal Response, Junction-to-Ambient

### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NRVTSS3100ET3G	SMB (Pb-Free)	2500 / Tape & Reel
NRVTSS3100ET3G-GA01	SMB (Pb-Free)	2500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

ON Semiconductor®



SCALE 1:1

Polarity Band



SCALE 1:1

Non-Polarity Band

**SMB**  
CASE 403A-03  
ISSUE J

DATE 19 JUL 2012



**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION b SHALL BE MEASURED WITHIN DIMENSION L1.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.95	2.30	2.47	0.077	0.091	0.097
A1	0.05	0.10	0.20	0.002	0.004	0.008
b	1.96	2.03	2.20	0.077	0.080	0.087
c	0.15	0.23	0.31	0.006	0.009	0.012
D	3.30	3.56	3.95	0.130	0.140	0.156
E	4.06	4.32	4.60	0.160	0.170	0.181
HE	5.21	5.44	5.60	0.205	0.214	0.220
L	0.76	1.02	1.60	0.030	0.040	0.063
L1	0.51 REF			0.020 REF		

**GENERIC MARKING DIAGRAM\***

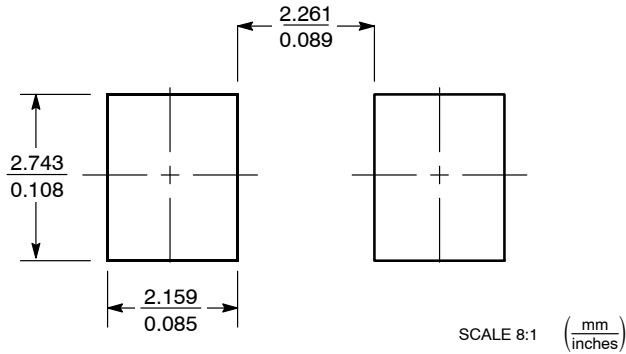


**Polarity Band      Non-Polarity Band**

- XXXXX = Specific Device Code
  - A = Assembly Location
  - Y = Year
  - WW = Work Week
  - = Pb-Free Package
- (Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

**SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

<b>DOCUMENT NUMBER:</b>	<b>98ASB42669B</b>	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
<b>DESCRIPTION:</b>	<b>SMB</b>	<b>PAGE 1 OF 1</b>

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

**onsemi**, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## ADDITIONAL INFORMATION

### TECHNICAL PUBLICATIONS:

Technical Library: [www.onsemi.com/design/resources/technical-documentation](http://www.onsemi.com/design/resources/technical-documentation)  
onsemi Website: [www.onsemi.com](http://www.onsemi.com)

### ONLINE SUPPORT: [www.onsemi.com/support](http://www.onsemi.com/support)

For additional information, please contact your local Sales Representative at [www.onsemi.com/support/sales](http://www.onsemi.com/support/sales)